

Features

- Split Gate Trench MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

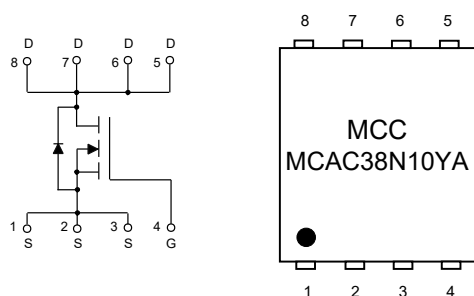
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 50°C/W Junction to Ambient (Note 2)
- Thermal Resistance: 2.1°C/W Junction to Case

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _C =25°C	I _D	38	A
	T _C =100°C		24	
Pulsed Drain Current ^(Note 3)		I _{DM}	152	A
Total Power Dissipation ^(Note 4)		P _D	60	W
Single Pulsed Avalanche Energy ^(Note 5)		E _{AS}	84	mJ

Note:

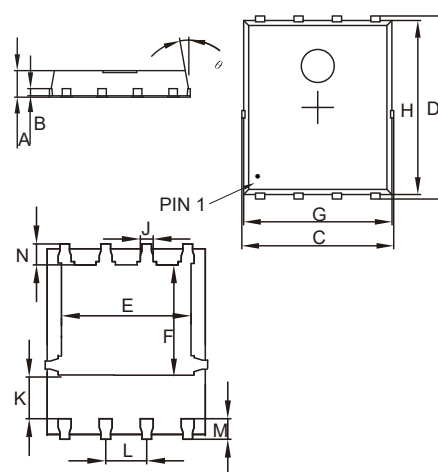
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. $T_J=25^\circ\text{C}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, $L=1\text{mH}$.

Internal Structure and Marking Code



N-CHANNEL MOSFET

DFN5060



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	100			V
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			0.3	μA
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	2.8	4	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		15.5	20	mΩ
		V _{GS} =6V, I _D =20A		19	25	
Gate Resistance	R _g	f=1MHz, Open drain		1.4		Ω
Diode Characteristics						
Continuous Body Diode Current	I _S				38	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =20A			1.2	V
Reverse Recovery Time	t _{rr}	I _F =20A, dI _F /dt=100A/μs		43		ns
Reverse Recovery Charge	Q _{rr}			51		nC
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz		1200		pF
Output Capacitance	C _{oss}			415		
Reverse Transfer Capacitance	C _{rss}			8.4		
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V, I _D =25A		15.7		nC
Gate-Source Charge	Q _{gs}			5.2		
Gate-Drain Charge	Q _{gd}			2.4		
Turn-On Delay Time	t _{d(on)}	V _{DD} =50V, V _{GEN} =10V, R _G =2.2Ω, I _{DS} =25A		9.5		ns
Turn-On Rise Time	t _r			3.3		
Turn-Off Delay Time	t _{d(off)}			15		
Turn-Off Fall Time	t _f			3		

Curve Characteristics

Fig. 1 Typical Output Characteristics

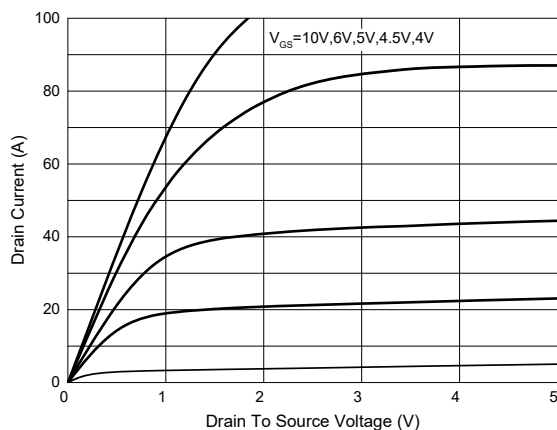


Fig.2 Transfer Characteristic

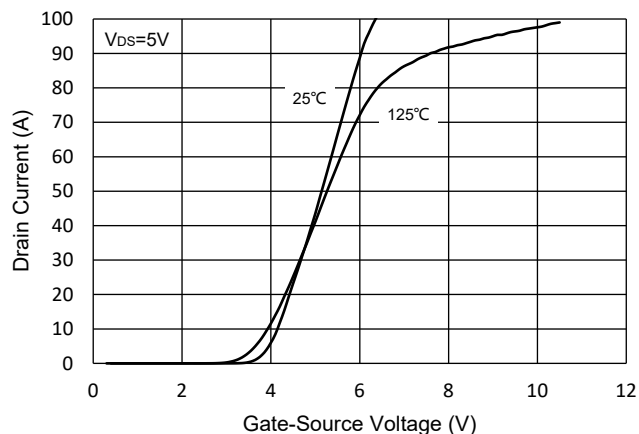


Fig.3 Rdson-Vgs

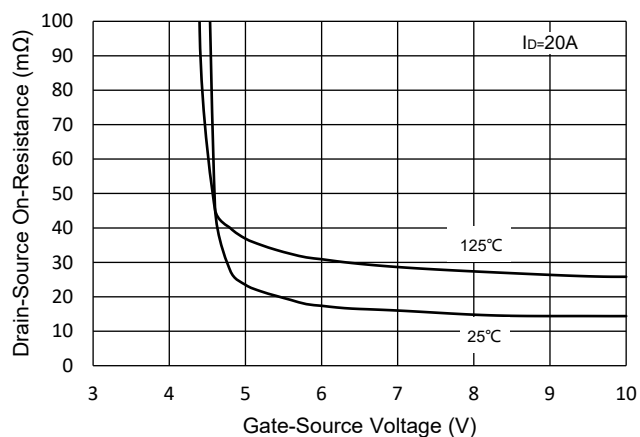


Fig.4 RDS(ON)-Id

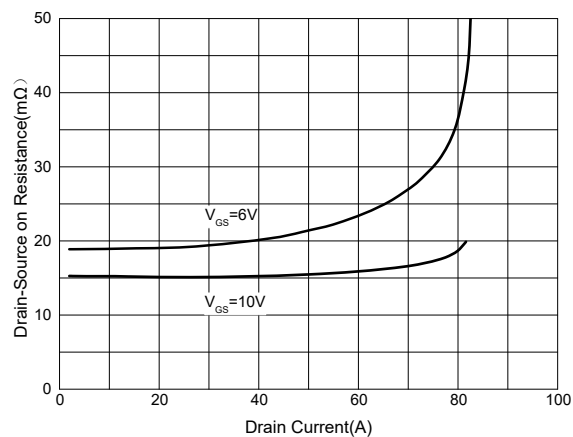


Fig.5 Capacitance Characteristics

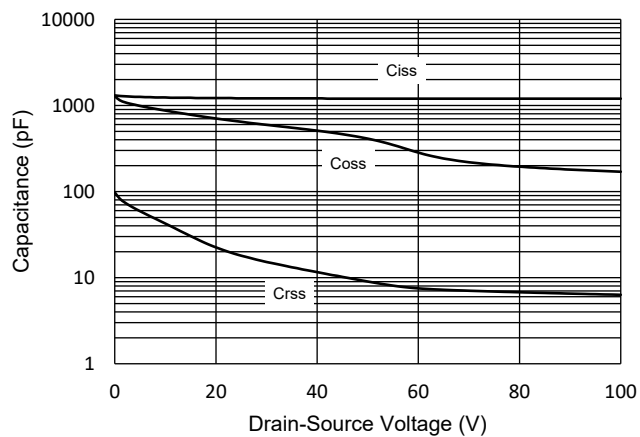
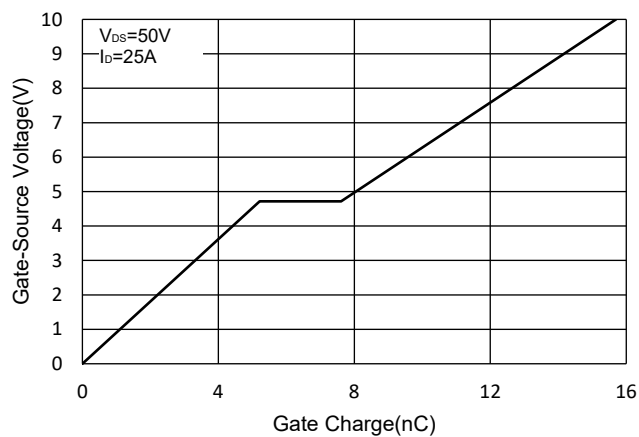


Fig.6 Gate Charge



Curve Characteristics

Fig.7 Normalized Threshold Voltage

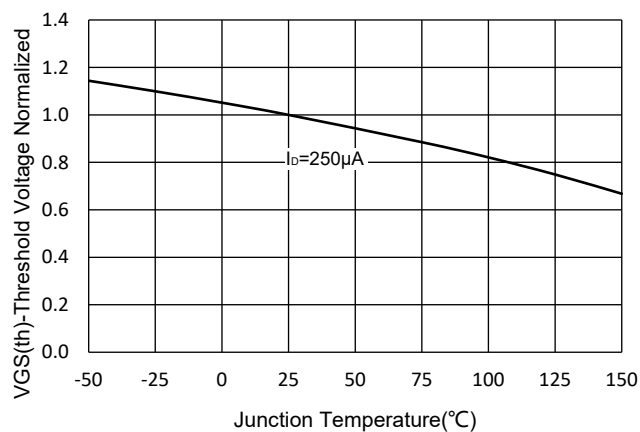


Fig.8 Normalized On Resistance Characteristics

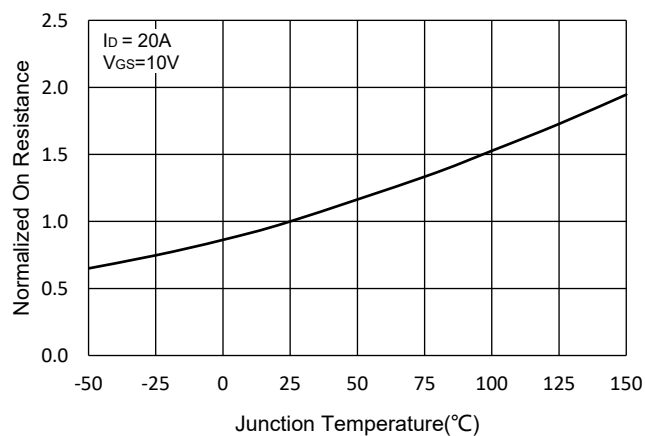


Fig.9 IS-VSD

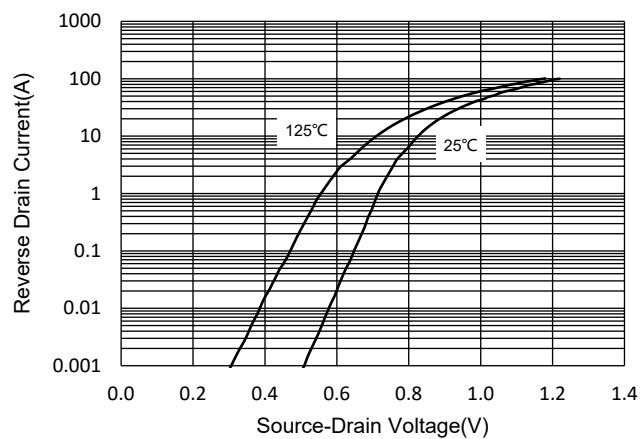


Fig.10 Drain Current

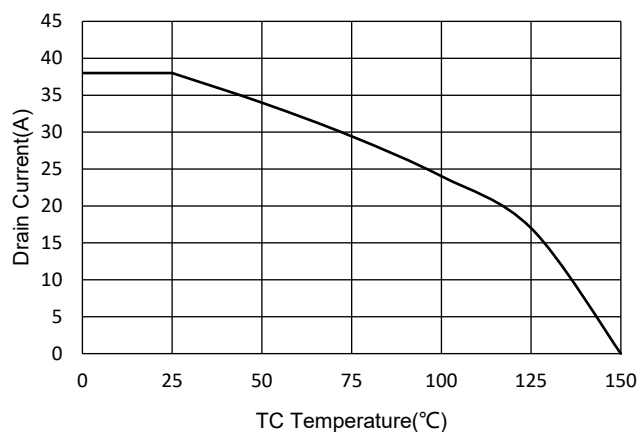
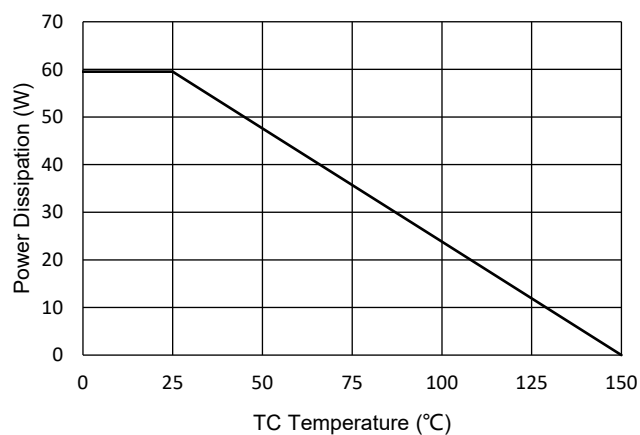


Fig.11 PD Dissipation



Curve Characteristics

Fig.12 Safe Operation Area

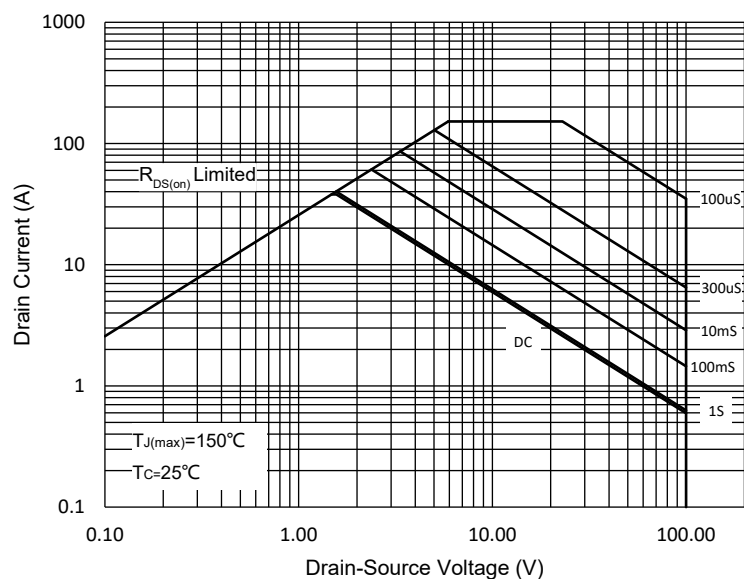
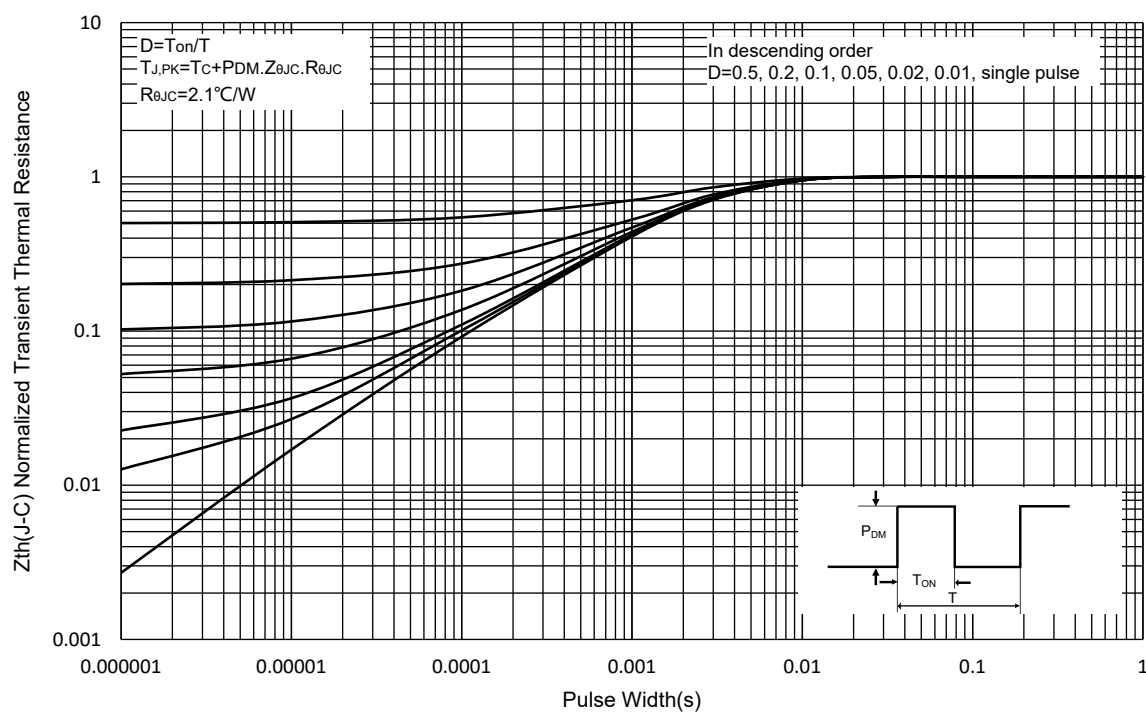


Fig.13 Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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